



BAV19 THRU BAV21

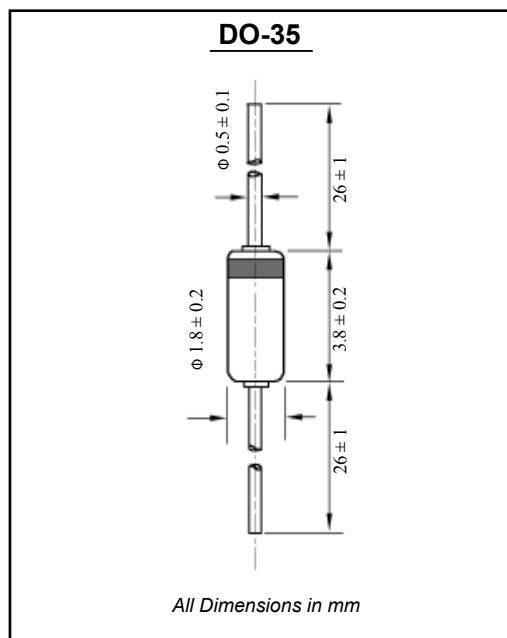
SMALL SIGNAL SWITCHING DIODE

FEATURES

- Silicon epitaxial planar diode
- Switching diodes
- 500mw power dissipation
- High temperature soldering guaranteed
250°C/10 seconds, 0.375" (9.5mm) lead length,
5 lbs. (2.3kg) tension

MECHANICAL DATA

- **Case:** DO-35 glass case
- **Polarity:** Color band denotes cathode end
- **Weight:** Approx. 0.13gram



Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless otherwise noted)

PARAMETER	SYMBOL	BAV19	BAV20	BAV21	UNITS
Reverse Voltage	V_R	100	150	200	V
Peak Reverse Voltage	V_{RM}	120	200	250	V
Rectified Current (Average), Half Wave Rectification with Resistive Load and $f \geq 50\text{Hz}$	$I_{F(AV)}$	200			mA
Peak Forward Surge Current, 1.0s	I_{FSM}	1.0			A
Power Dissipation Derate Above 25°C	P_{tot}	500			mW
Maximum Forward Voltage at 0.1A	V_F	1.0			V
Maximum DC Reverse Current at Rated DC Blocking Voltage $T_J=25^{\circ}\text{C}$	I_R	0.1			μA
Typical Junction Capacitance(Notes1)	C_J	3.0			pF
Maximum Reverse Recovery (Notes2)	t_{rr}	50			ns
Typical Thermal Resistance	$R_{\theta JA}$	350			$^{\circ}\text{C} / \text{W}$
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 to +150			$^{\circ}\text{C}$

NOTE:

1. C_J at $V_R=0$, $f=1\text{MHz}$
2. From $I_F=30\text{mA}$ to $I_R=-3\text{mA}$, $V_R=6\text{Volts}$, $R_L=100\Omega$



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RATINGS AND CHARACTERISTIC CURVES

